

N-Channel Enhancement Mode Field Effect Transistor

General Description

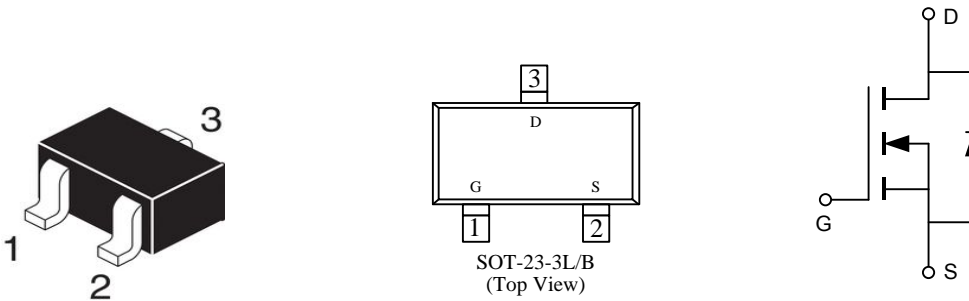
Product Summary		
V_{DS}	I_D	$R_{DS(ON)}(m\Omega)TYP$
20V	3.6A	33 @ $V_{GS} = 4.5V$
		52 @ $V_{GS} = 2.5V$

Features

- Super high dense cell design for low $R_{DS(ON)}$
- Rugged and reliable
- Simple drive requirement
- SOT-23-3L/B package

Package

- SOT-23-3L/B



Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
PN2300	-55°C to +150°C	SOT-23-3L/B	3000

Absolute Maximum Ratings

($T_A=25^\circ C$ unless otherwise noted)

parameter	symbol	limit	unit
Drain-source voltage	V_{DS}	20	V
Gate-source voltage	V_{GS}	± 8	V
Drain current-continuous ^a @ $T_j=125^\circ C$ -pulse d^b	I_D	3.6	A
	I_{DM}	12	A
Drain-source Diode forward current	I_S	1.25	A
Maximum power dissipation	P_D	1.25	W
Operating junction Temperature range	T_j	-55—150	$^\circ C$